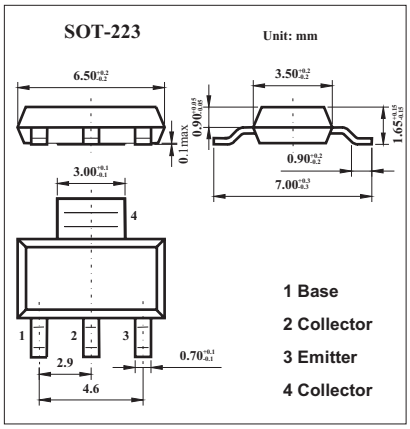
NPN Silicon Extremely High Voltage Transistor

CZTA44



■ Features

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■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	450	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	300	mA
Power Dissipation	P_D	2	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to 150	℃
Thermal Resistance	Θ_{JA}	62.5	℃/W

■ Electrical Characteristics Ta = 25℃

Symbol	Testconditons	Min	Max	Unit
I_{CBO}	V_{CB}=400V		100	nA
I_{CES}	V_{CE}=400V		500	nA
I_{EBO}	V_{BE}=4.0V		100	nA
B_{VCBO}	I_C=100μA	450		V
B_{VCES}	I_C=100μA	450		V
B_{VCEO}	I_C=1.0mA	400		V
B_{VEBO}	I_E=10μA	6.0		V
$V_{CE(SAT)}$	I_C=1.0mA, I_B=0.1mA		0.40	V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA		0.50	V
$V_{CE(SAT)}$	I_C=50mA, I_B=5.0mA		0.75	V
$V_{BE(SAT)}$	I_C=10mA, I_B=1.0mA		0.75	V
h_{FE}	V_{CE}=10V, I_C=1.0mA	40		
	V_{CE}=10V, I_C=10mA	50	200	
	V_{CE}=10V, I_C=50mA	45		
	V_{CE}=10V, I_C=100mA	20		
f_T	V_{CE}=10V, I_C=10mA, f=10MHz	20		MHz
C_{ob}	V_{CB}=20V, I_E=0, f=1.0MHz		7.0	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=1.0MHz		130	pF